Silicon NPN Power Transistors 2SD386 2SD386A

DESCRIPTION

·With TO-220C package

·High voltage :V_{CBO}=200V(min)

APPLICATIONS

·For TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

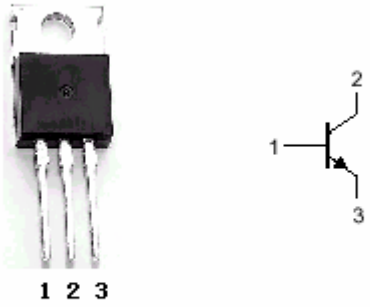

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	200	V
V_{CEO}	Collector-emitter voltage	2SD386	Open base	120	V
		2SD386A		150	
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current	2SD386		3	A
		2SD386A		2	
I_{CM}	Collector current-Peak			10	A
P_C	Collector dissipation		T_C=25□	25	W
			T_a=25□	1.75	
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-40~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SD386	I_C=25mA; I_B=0	120			V
		2SD386A		150			
V_{CEsat}	Collector-emitter saturation voltage	2SD386	I_C=1A; I_B=0.1A			1.0	V
		2SD386A				1.5	
V_{BEsat}	Base-emitter saturation voltage		I_C=1A; I_B=0.1A			1.8	V
I_{CBO}	Collector cut-off current		V_{CB}=180V; I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			5.0	mA
h_{FE}	DC current gain		I_C=0.5A ; V_{CE}=2V	40		320	
f_T	Transition frequency		I_C=0.5A ; V_{CE}=5V		8		MHz

◆ **h_{FE} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320

PACKAGE OUTLINE

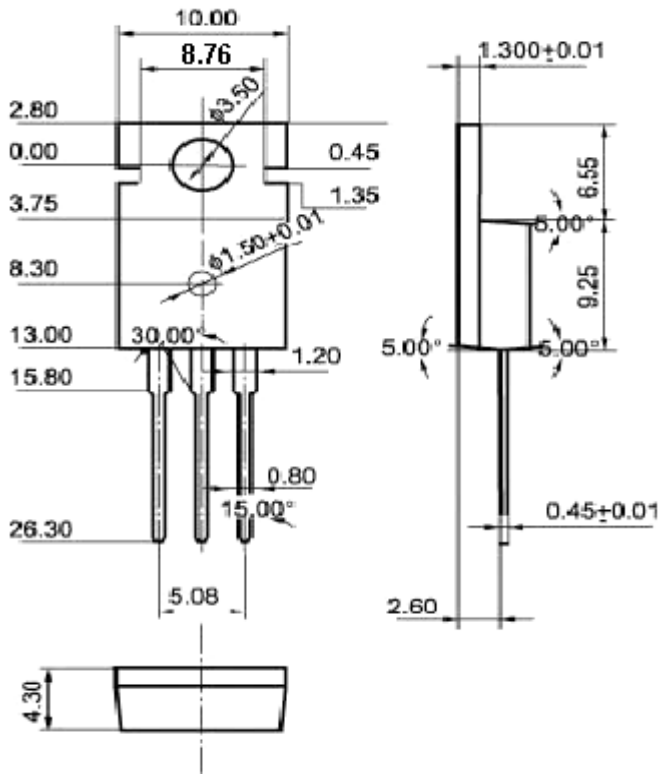

Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)